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OA1182

Gold Bonded Germanium Diode

FEATURES

Low forward voltage drop—low power consumption

Thirty years of proven reliability—one million hours mean time between failures (MTBF)

Very low noise level

Metallurgically bonded

ABSOLUTE MAXIMUM RATINGS (at 25 °C, unless otherwise specified)

Peak Inverse Voltage 100 Volts

Peak Forward Current 500 mA

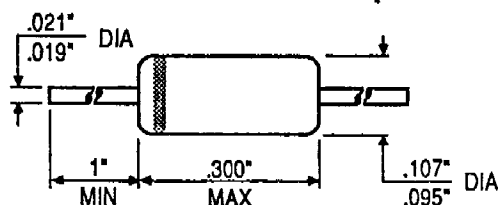
Operating Temperature - 65 °C to 85 °C

Average Power Dissipation 80 mW

ELECTRICAL CHARACTERISTICS

	Symbol	Conditions	Min	Max	Unit	T °C
Peak Inverse Voltage	PIV	1 mA	100		V	25 °C
Reverse Current	I _r	60 V		20	μA	25 °C
Forward Voltage	V _f	100 mA		0.85	V	25 °C

MECHANICAL



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